

Amendments to the Claims:

The following listing will replace all prior listing of claims in the application.

Listing of Claims:

1. (Currently amended) A method of fabricating a die containing an integrated circuit comprising active components and passive components, the method comprising:

producing a first substrate containing including at least one active component and

producing a second substrate containing including critical passive components; and

bonding the two first and second substrates, wherein the bonding comprises performing a layer transfer through molecular adhesion; and

after bonding of the first and second substrates, producing at least one interconnection line between the components of said first and second substrates, said interconnection line passing through the second substrate.

2. (Previously presented) A method according to claim 1, wherein said at least one active component comprises transistors.

3. (Previously presented) A method according to claim 1, wherein said critical passive components comprise at least one capacitor and at least one microelectromechanical system (MEMS).

4. (Currently amended) A method according to claim 1 wherein said critical passive components comprise at least one of one capacitor or at least one microelectromechanical system (MEMS).

5. (Previously presented) A method according to claim 3, wherein a dielectric material of said at least one capacitor comprises a perovskite.

6. (Previously presented) A method according to claim 1, wherein producing said second substrate comprises producing an electrically conductive material.

7. (Previously presented) A method according to claim 1, wherein producing said second substrate comprises producing a dielectric material.

8. (Previously presented) A method according to claim 7, wherein producing said second substrate comprises producing perovskite.

9. (Currently amended) A method according to ~~claim 8~~ claim 1 further comprising producing dielectric insulation trenches in said second substrate during the production of said second substrate.

10. (Currently amended) A method according to ~~claim 9~~ claim 1 further comprising producing at least one non-critical passive component during the production of said second substrate.

11. (Currently amended) A method according to ~~claim 9~~ claim 10, wherein producing the non-critical passive component comprises producing a capacitor in trenches.

12. (Previously presented) A method according to claim 9 further comprising producing at least one inductor in the vicinity of a face of the second substrate opposite a bonding face after said bonding of the two substrates.

13. (Currently amended) A method according to claim 12 further comprising producing said at least one inductor ~~produced on said inductive~~ dielectric insulation trenches ~~previously produced in said second substrate~~.

14. (Cancelled)

15. (Currently amended) A die fabricated by a method according to ~~claim 13~~ claim 1.

16. (Currently amended) A die containing an integrated circuit comprising active components and passive components and including a single stack of layers, wherein said die comprises an interface between two of said layers such that a ~~said~~ first portion

of the die situated on one side of said interface ~~contains~~ includes at least one active component of said active components and a second ~~said~~ portion of said die ~~contains~~ includes critical ~~passive~~ components of said passive components, ~~the die comprising at least one interconnection line between the components of said first and second portions, said interconnection line passing through the second portion.~~

17. (Previously presented) A die according to claim 16 wherein said critical passive components comprise at least one capacitor and at least one MEMS enclosed in a cavity situated inside said die.

18. (Cancelled)

19. (Currently amended) A die according to claim 17, wherein the at least one capacitor comprises a dielectric material comprising perovskite.

20. (Currently amended) A die according to ~~claim 17~~ claim 16, wherein -said die further comprises dielectric insulation trenches.

21. (Currently amended) A die according to ~~claim 18~~ claim 16, wherein said integrated circuit further comprises at least one non-critical passive component.

22. (Previously presented) A die according to claim 21 wherein said non-critical passive component comprises a capacitor in trenches.

23. (Currently amended) A die according to ~~claim 18~~ claim 16, wherein said active components are disposed in the vicinity of a first face of the die and wherein said integrated circuit further comprises at least one inductor situated in a vicinity of said face of the die opposite said first face.

24. (Currently amended) A die according to ~~claim 22~~ claim 23, wherein said at least one inductor is situated on inductive insulation trenches.

25. (Currently amended) A die according to any one of ~~claim 21~~ claim 16, wherein said active components are disposed in a vicinity of a first face of said die (100)

and said die further comprises at least one interconnection line that emerges in the vicinity of said face of said die opposite said first face.

26. (Currently amended) A die according to any one of claim 21 wherein said active components are disposed in a vicinity of a first face of said die (100) and said die further comprises at least one interconnection line that emerges in the vicinity of said face of said die opposite said first face.

27. (New) A method according to claim 13, wherein said at least one inductor and at least one of said interconnection lines are produced during a same process step.